

Applications

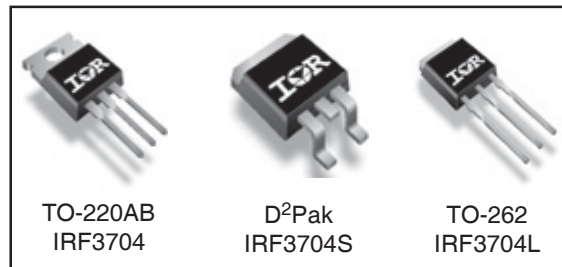
- High Frequency DC-DC Isolated Converters with Synchronous Rectification for Telecom and Industrial use
- High Frequency Buck Converters for Computer Processor Power
- Lead-Free

HEXFET® Power MOSFET

V_{DS}	$R_{DS(on)}$ max	I_D
20V	9.0m Ω	77A ^⑤

Benefits

- Ultra-Low Gate Impedance
- Very Low $R_{DS(on)}$
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	77 ^⑤	A
I_D @ $T_C = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	64	
I_{DM}	Pulsed Drain Current ^①	308	
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation ^③	87	W
P_D @ $T_C = 70^\circ\text{C}$	Maximum Power Dissipation ^③	61	W
	Linear Derating Factor	0.59	mW/ $^\circ\text{C}$
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 175	$^\circ\text{C}$

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.73	$^\circ\text{C/W}$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface ^④	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ^④	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	—	40	

* When mounted on 1" square PCB (FR-4 or G-10 Material) .
For recommended footprint and soldering techniques refer to application note #AN-994

Notes ① through ④ are on page 10

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IRF3704/S/LPbF

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.021	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.3	9.0	$m\Omega$	$V_{GS} = 10V, I_D = 15A$ ③
		—	9.8	13.5		$V_{GS} = 4.5V, I_D = 12A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	42	—	—	S	$V_{DS} = 10V, I_D = 57A$
Q_g	Total Gate Charge	—	19	—	nC	$I_D = 28.4A$
Q_{gs}	Gate-to-Source Charge	—	8.1	—		$V_{DS} = 10V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	6.4	—		$V_{GS} = 4.5V$ ③
Q_{oss}	Output Gate Charge	—	16	24		$V_{GS} = 0V, V_{DS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	8.4	—	ns	$V_{DD} = 10V$
t_r	Rise Time	—	98	—		$I_D = 28.4A$
$t_{d(off)}$	Turn-Off Delay Time	—	12	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	5.0	—		$V_{GS} = 4.5V$ ③
C_{iss}	Input Capacitance	—	1996	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1085	—		$V_{DS} = 10V$
C_{rss}	Reverse Transfer Capacitance	—	155	—		$f = 1.0MHz$

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	216	mJ
I_{AR}	Avalanche Current①	—	71	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	77⑤	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	308		
V_{SD}	Diode Forward Voltage	—	0.88	1.3	V	$T_J = 25^\circ\text{C}, I_S = 35.5A, V_{GS} = 0V$ ③
		—	0.82	—		$T_J = 125^\circ\text{C}, I_S = 35.5A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	38	57	ns	$T_J = 25^\circ\text{C}, I_F = 35.5A, V_R = 20V$
Q_{rr}	Reverse Recovery Charge	—	45	68	nC	$di/dt = 100A/\mu s$ ③
t_{rr}	Reverse Recovery Time	—	41	62	ns	$T_J = 125^\circ\text{C}, I_F = 35.5A, V_R = 20V$
Q_{rr}	Reverse Recovery Charge	—	50	75	nC	$di/dt = 100A/\mu s$ ③

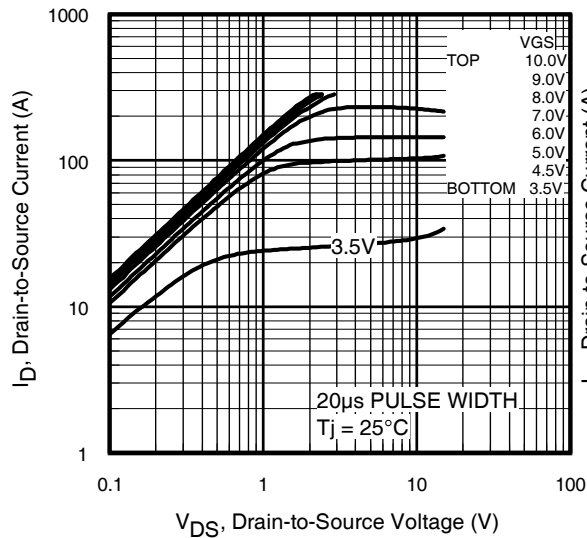


Fig 1. Typical Output Characteristics

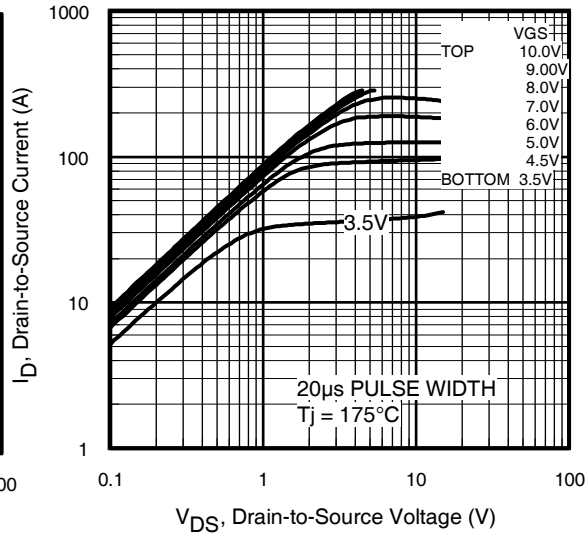


Fig 2. Typical Output Characteristics

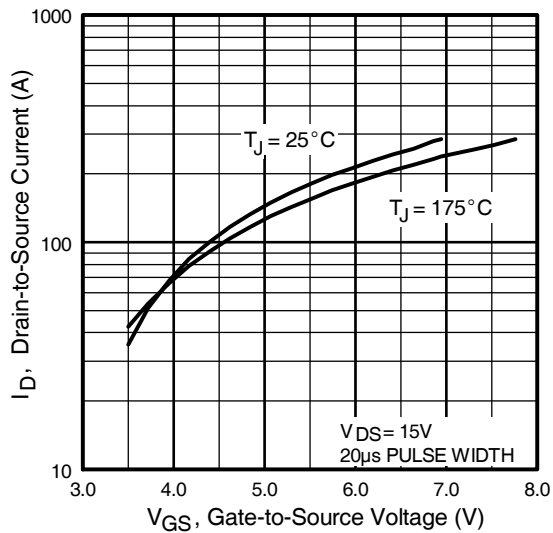


Fig 3. Typical Transfer Characteristics

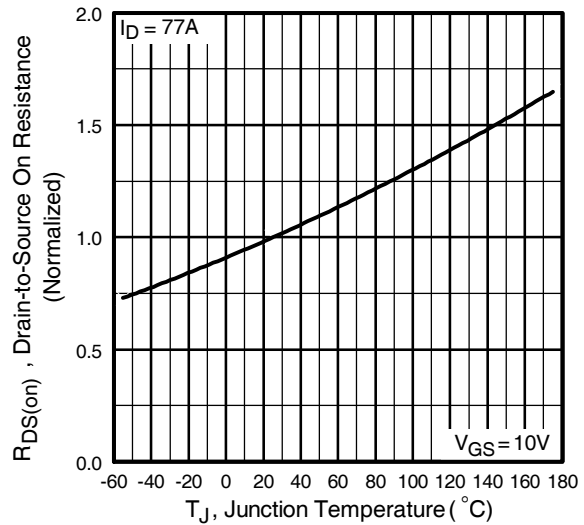


Fig 4. Normalized On-Resistance Vs. Temperature

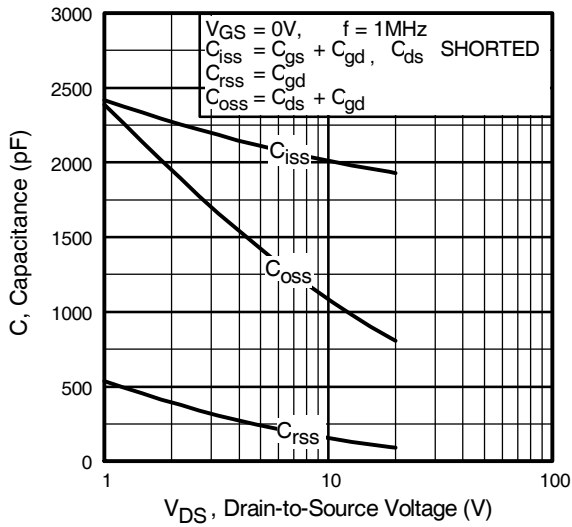


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

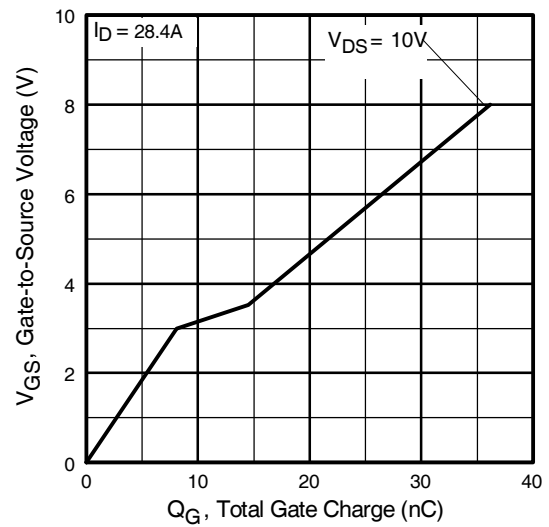


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

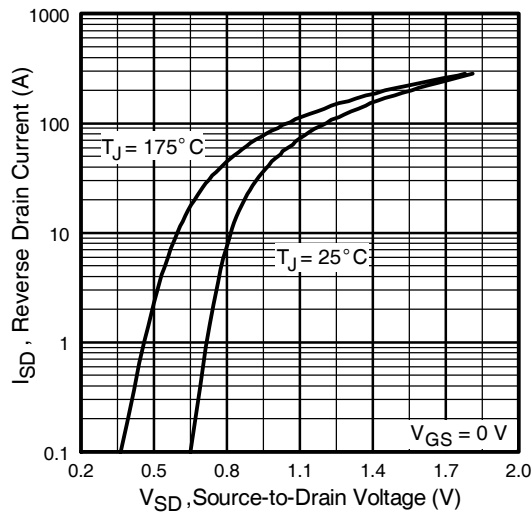


Fig 7. Typical Source-Drain Diode Forward Voltage

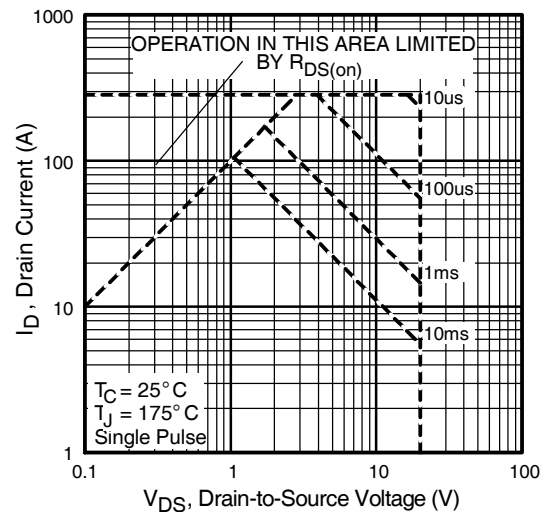


Fig 8. Maximum Safe Operating Area

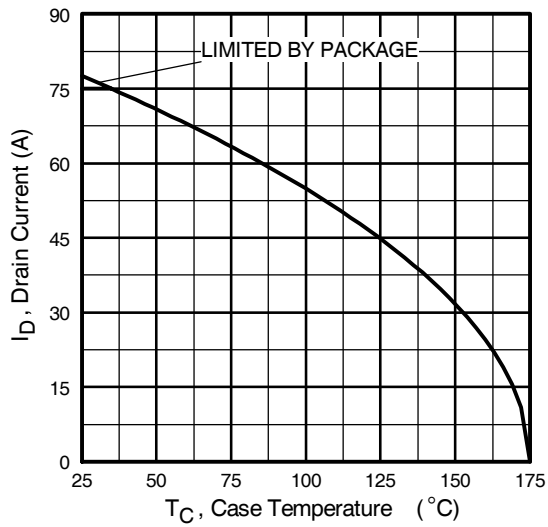


Fig 9. Maximum Drain Current Vs. Case Temperature

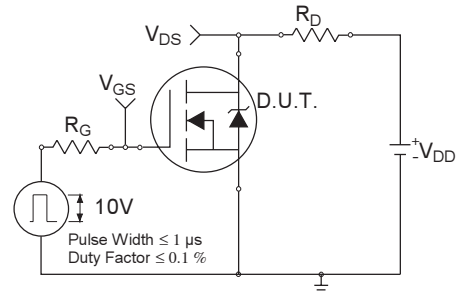


Fig 10a. Switching Time Test Circuit

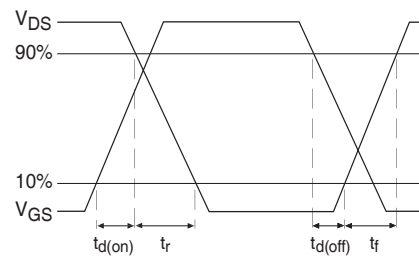


Fig 10b. Switching Time Waveforms

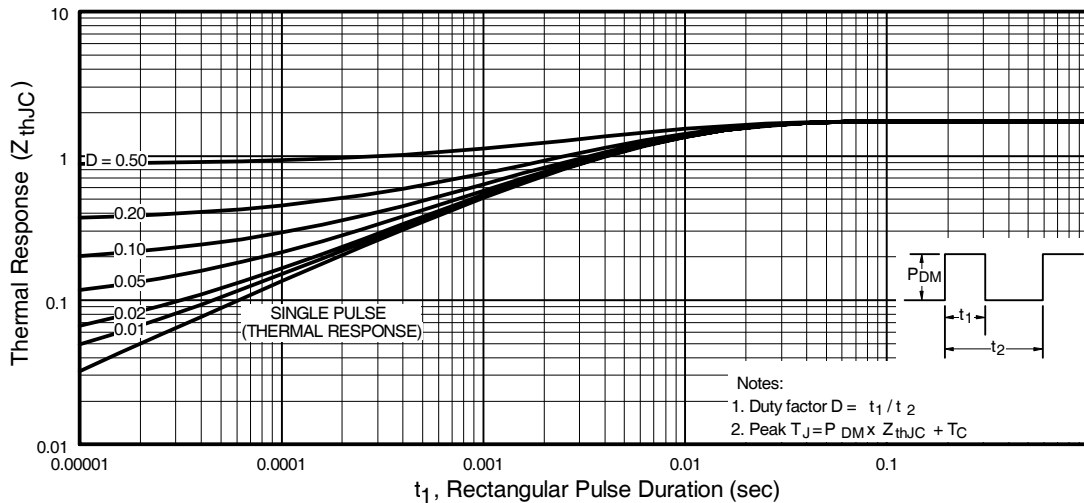


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

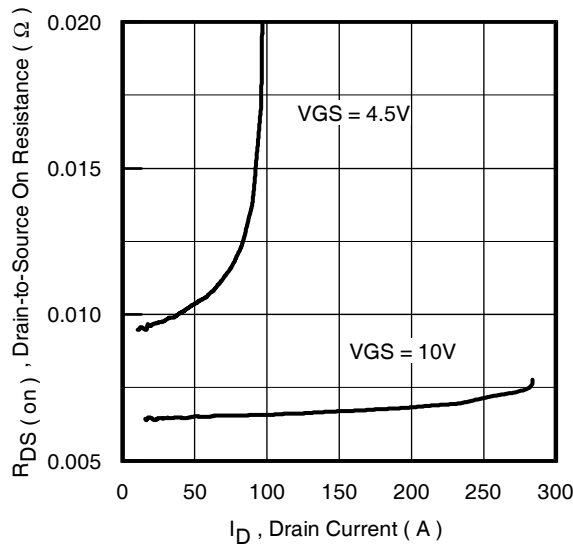


Fig 12. On-Resistance Vs. Drain Current

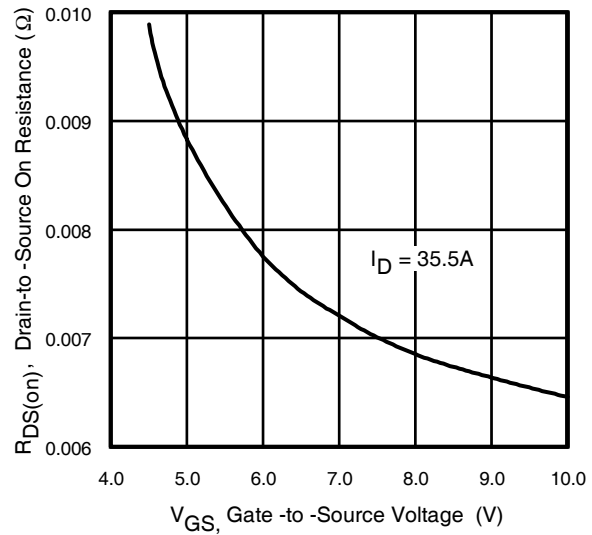


Fig 13. On-Resistance Vs. Gate Voltage

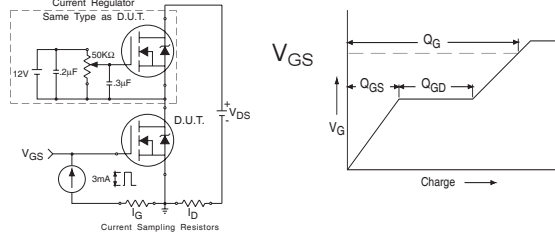


Fig 14a&b. Basic Gate Charge Test circuit and Waveforms

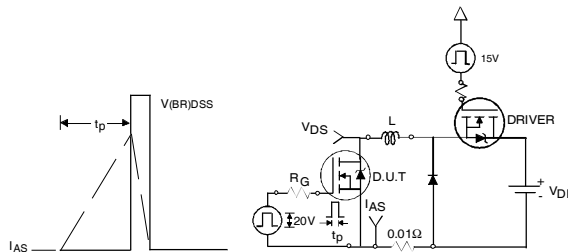


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

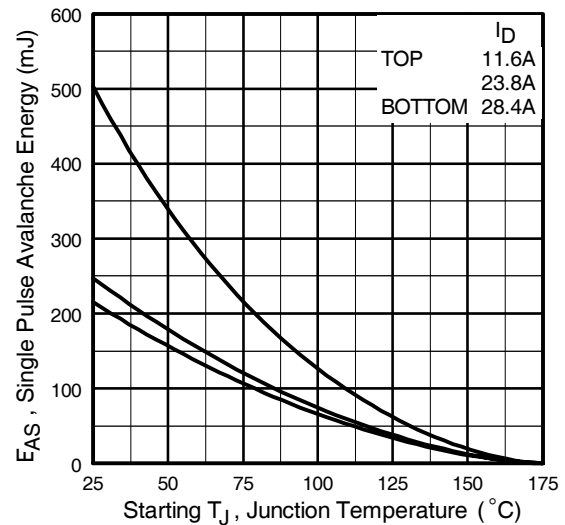
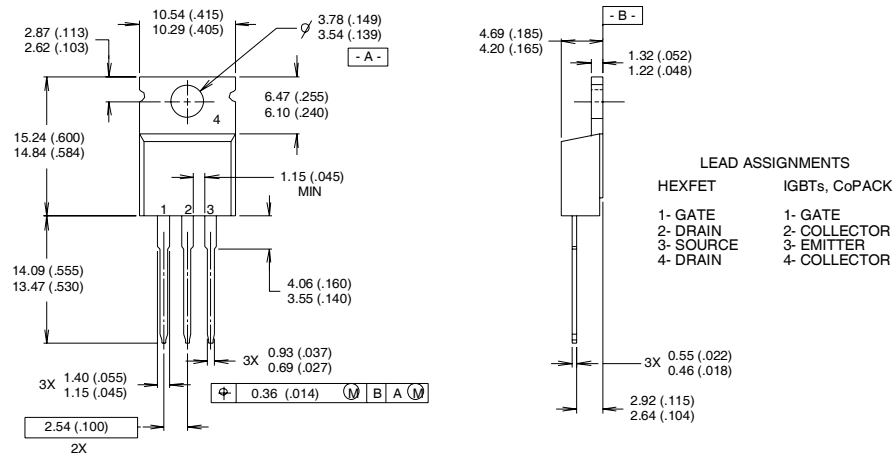


Fig 15c. Maximum Avalanche Energy Vs. Drain Current

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

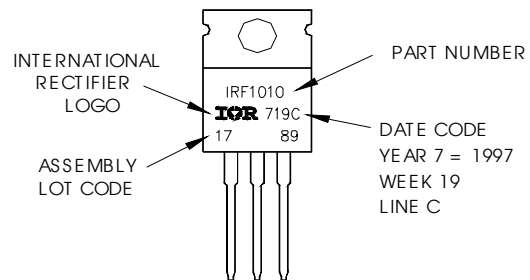
EXAMPLE: THIS IS AN IRF1010

LOT CODE 1789

ASSEMBLED ON WW 19, 1997

IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

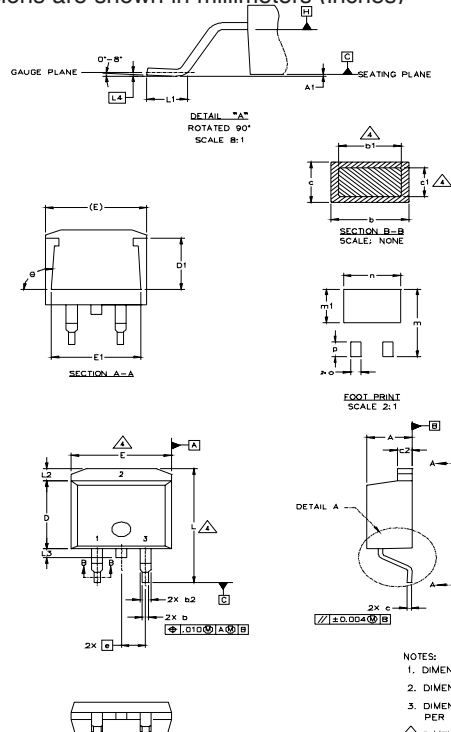


IRF3704/S/LPbF

International
IR Rectifier

D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		3
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

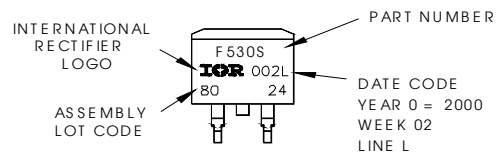
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 (.005") PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

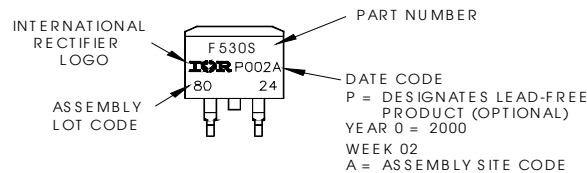
D²Pak Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

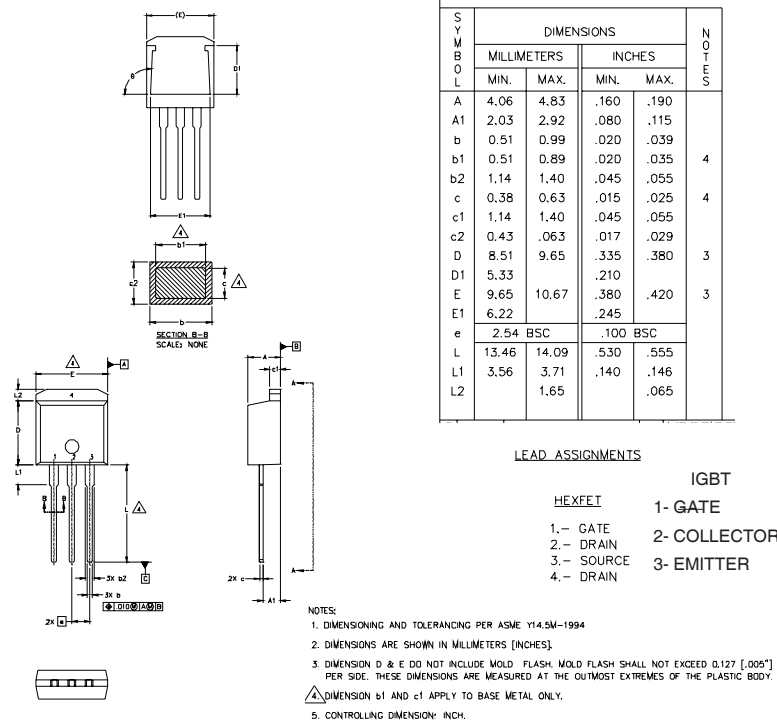
Note: "P" in assembly line
position indicates "Lead-Free"



OR



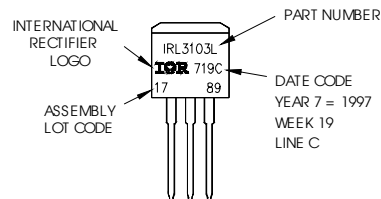
TO-262 Package Outline



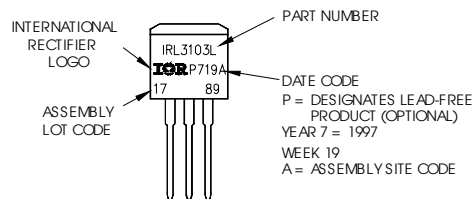
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

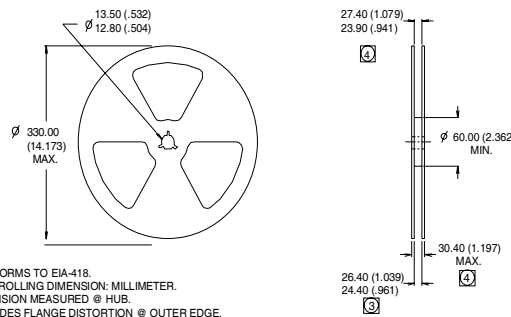
Note: "P" in assembly line position indicates "Lead-Free"



OR



International
IOR Rectifier



- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}\text{C}$, $L = 0.5\text{ mH}$
 $R_G = 25\Omega$, $I_{AS} = 28.4\text{ A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ This is only applied to TO-220AB package
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.

International
IOR Rectifier

www.irf.com

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>